Reg. No.:....

Name :

Seventh Semester B.Tech. Degree Examination, June 2016 (2008 Scheme) 08.735 : OPTOELECTRONIC DEVICES (TA) (Elective – III)

Time: 3 Hours

Max. Marks: 100

PART-A

Answerall questions.

1. Briefly explain radiative and non radiative recombination.

2. Compare the performance of p-i-n photodiode and p n photo diode.

3. What is luminescence? What are the types of luminescence?

- 4. Explain deep level transitions.
- 5. Describe the principle of LED.
- 6. What are the applications of optoelectronic modulators?
- 7. Compare MS and MSM photodiodes.
- Describe the process of spontaneous emission super radiance and stimulated emission.
- Discuss some advantages that the laser may have over an LED as a source of optical fiber communication.
- Calculate the ratio of spontaneous to stimulated emission rates in a tungsten lamp that radiates an average frequency of 5×10¹⁴ Hz at an operating temperature of 1300°K.
 (10×4=40 Marks)

PART-B

Answer two questions from each Module.

Module -I

- 11. Briefly explain the absorption and radiation mechanisms in a semi conductor.
- 12. Explain the techniques used to measure the high speed response of diodes.
- 13. Explain:
 - a) Hetero junction diodes.
 - b) Noise performance of avalanche photo diodes.

(2×10=20 Marks)

P.T.O.



Module - II

- 14. Write short notes on:
 - a) MS photodiode
 - b) MSM photodiode.
- 15. Derive the efficiency of LED.
- 16. Write short note on:
 - a) Wavelength selective detection.
 - b) Coherent detection.

(2×10=20 Marks)

Module - III

- 17. Describe with suitable diagrams, the principle of hetero junction laser.
- 18. Explain the operating principles of junction laser and its threshold current with all necessary equations.
- 19. a) How can we find the gami in a two level lasing medium?
 - b) Find the spectral output (number of modes) of an AlGa As laser supported by the gain spectrum which has a bandwidth of 6 nm. The laser has a cavity length of 200 μ m and emission wavelength of 800 nm. (2×10=20 Marks)